

<HVIC>

# M81776FP

600V HIGH VOLTAGE HALF BRIDGE DRIVER

## DESCRIPTION

M81776FP is high voltage Power MOSFET and IGBT gate driver for half bridge applications.

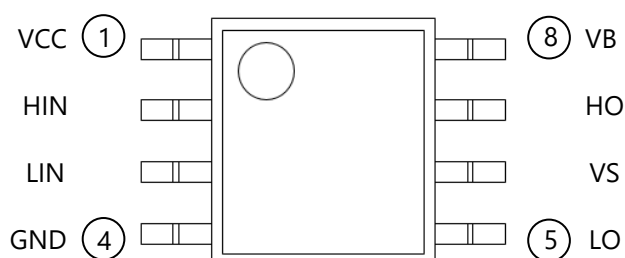
## FEATURES

- Floating Supply Voltage ..... 600V
- Output Current ..... +200mA/-350mA
- Half Bridge Driver
- Protect supply voltage drop
- SOP-8 Package

## APPLICATIONS

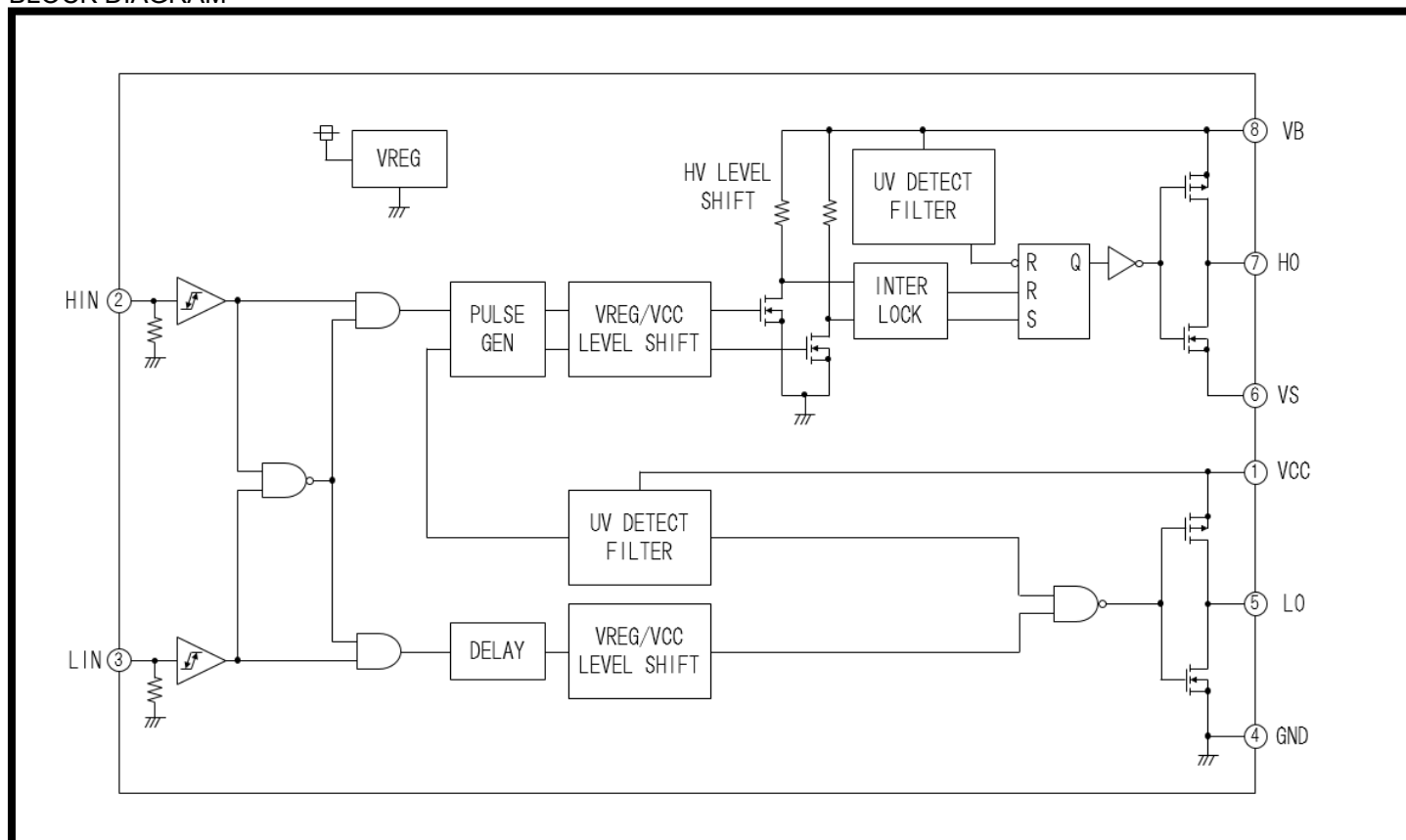
MOSFET and IGBT module driver.

## PIN CONFIGURATION (TOP VIEW)



Outline:SOP8

## BLOCK DIAGRAM



**M81776FP**

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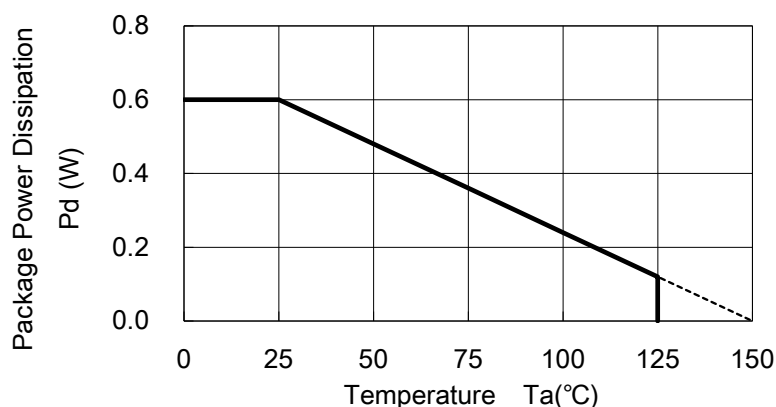
**ABSOLUTE MAXIMUM RATINGS (Ta = 25°C unless otherwise specified)**

Symbol	Parameter	Test conditions	Ratings	Unit
V <sub>B</sub>	High Side Floating Supply Absolute Voltage		- 0.5 ~ 624	V
V <sub>S</sub>	High Side Floating Supply Offset Voltage		V <sub>B</sub> - 24 ~ V <sub>B</sub> + 0.5	V
V <sub>BS</sub>	High Side Floating Supply Voltage	V <sub>BS</sub> = V <sub>B</sub> - V <sub>S</sub>	- 0.5 ~ 24	V
V <sub>HO</sub>	High Side Output Voltage		V <sub>S</sub> - 0.5 ~ V <sub>B</sub> + 0.5	V
V <sub>CC</sub>	Low Side Fixed Supply Voltage		- 0.5 ~ 24	V
V <sub>LO</sub>	Low Side Output Voltage		- 0.5 ~ V <sub>CC</sub> + 0.5	V
V <sub>IN</sub>	Logic Input Voltage	HIN,LIN Terminal	- 0.5 ~ V <sub>CC</sub> + 0.5	V
P <sub>d</sub>	Package Power Dissipation	Ta = 25°C ,On Board	0.6	W
Kθ	Linear Derating Factor	Ta > 25°C ,On Board	4.8	mW/°C
R <sub>th(j-c)</sub>	Junction-Case Thermal Resistance		50	°C/W
T <sub>j</sub>	Junction Temperature		- 40 ~ 150	°C
T <sub>opr</sub>	Operation Temperature		- 40 ~ 125	°C
T <sub>stg</sub>	Storage Temperature	On Board	- 40 ~ 150	°C
TL	Solder Reflow Condition	Pb-free	255:10s, max 260	°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V <sub>B</sub>	High Side Floating Supply Absolute Voltage		V <sub>S</sub> + 10	—	V <sub>S</sub> + 20	V
V <sub>S</sub>	High Side Floating Supply Offset Voltage		0	—	500	V
V <sub>BS</sub>	High Side Floating Supply Voltage	V <sub>BS</sub> = V <sub>B</sub> - V <sub>S</sub>	10	—	20	V
V <sub>HO</sub>	High Side Output Voltage		V <sub>S</sub>	—	V <sub>B</sub>	V
V <sub>CC</sub>	Low Side Fixed Supply Voltage		10	—	20	V
V <sub>LO</sub>	Low Side Output Voltage		0	—	V <sub>CC</sub>	V
V <sub>IN</sub>	Logic Input Voltage	HIN,LIN Terminal	0	—	V <sub>CC</sub>	V

Note : For proper operation, the device should be used within the recommended conditions

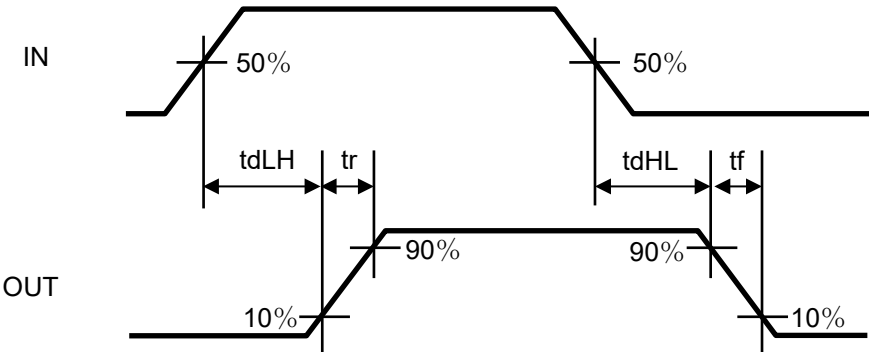
**THERMAL DERATING FACTOR CHARACTERISTIC (MAXIMUM RATING)**

**ELECTRICAL CHARACTERISTICS (Ta=25°C, VCC=VBS (=VB-VS)=15V, unless otherwise specified)**

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.*	Max.	
$I_{FS}$	Floating Supply Leakage Current	$V_B = V_S = 600V$	—	—	1.0	μA
$I_{BS}$	$V_{BS}$ Standby Current	$HIN = LIN = 0V$	—	0.2	0.5	mA
$I_{CC}$	$V_{CC}$ Standby Current	$HIN = LIN = 0V$	0.2	0.5	1.0	mA
$V_{OH}$	High Level Output Voltage	$I_O = -20mA$ HO,LO Terminal	13.6	14.2	—	V
$V_{OL}$	Low Level Output Voltage	$I_O = 20mA$ HO,LO Terminal	—	0.3	0.6	V
$V_{IH}$	High Level Input Threshold Voltage	HIN,LIN Terminal	2.7	—	—	V
$V_{IL}$	Low Level Input Threshold Voltage	HIN,LIN Terminal	—	—	0.8	V
$I_{IH}$	High Level Input Bias Current	$V_{IN} = 5V$	—	25	100	μA
$I_{IL}$	Low Level Input Bias Current	$V_{IN} = 0V$	—	—	2	μA
$V_{BSuvr}$	$V_{BS}$ Supply UV Reset Voltage		7.0	8.4	9.8	V
$V_{BSuvt}$	$V_{BS}$ Supply UV Trip Voltage		6.5	7.85	9.0	V
$V_{BSuvh}$	$V_{BS}$ Supply UV Hysteresis Voltage		0.3	0.55	—	V
$t_{VBSuv}$	$V_{BS}$ Supply UV Filter Time		—	7.5	—	us
$V_{CCuvr}$	$V_{CC}$ Supply UV Reset Voltage		7.0	8.4	9.8	V
$V_{CCuvt}$	$V_{CC}$ Supply UV Trip Voltage		6.5	7.85	9.0	V
$V_{CCuvh}$	$V_{CC}$ Supply UV Hysteresis Voltage		0.3	0.55	—	V
$t_{VCCuv}$	$V_{CC}$ Supply UV Filter Time		—	7.5	—	us
$I_{OH}$	Output High Level Short Circuit Pulsed Current	$V_O = 0V, V_{IN} = 5V, PW < 10ms$	120	200	—	mA
$I_{OL}$	Output Low Level Short Circuit Pulsed Current	$V_O = 15V, V_{IN} = 0V, PW < 10ms$	250	350	—	mA
$R_{OH}$	Output High Level On Resistance	$I_O = -20mA, R_{OH} = (V_{OH} - V_O) / I_O$	—	40	70	Ω
$R_{OL}$	Output Low Level On Resistance	$I_O = 20mA, R_{OL} = V_{OL} / I_O$	—	15	30	Ω
$t_{dLH}(HO)$	High Side Turn-On Propagation Delay	$CL = 1000pF$ between HO - $V_S$	—	150	300	ns
$t_{dHL}(HO)$	High Side Turn-Off Propagation Delay	$CL = 1000pF$ between HO - $V_S$	—	130	230	ns
$t_{rH}$	High Side Turn-On Rise Time	$CL = 1000pF$ between HO - $V_S$	—	130	220	ns
$t_{fH}$	High Side Turn-Off Fall Time	$CL = 1000pF$ between HO - $V_S$	—	50	80	ns
$t_{dLH}(LO)$	Low Side Turn-On Propagation Delay	$CL = 1000pF$ between LO - GND	—	150	300	ns
$t_{dHL}(LO)$	Low Side Turn-Off Propagation Delay	$CL = 1000pF$ between LO - GND	—	130	230	ns
$t_{rL}$	Low Side Turn-On Rise Time	$CL = 1000pF$ between LO - GND	—	130	220	ns
$t_{fL}$	Low Side Turn-Off Fall Time	$CL = 1000pF$ between LO - GND	—	50	80	ns
$DtdLH$	Turn-On Propagation Delay Matching	$ t_{dLH}(HO) - t_{dLH}(LO) $	—	0	30	ns
$DtdHL$	Turn-Off Propagation Delay Matching	$ t_{dHL}(HO) - t_{dHL}(LO) $	—	0	30	ns

\* Typ is not specified

INPUT/OUTPUT TIMING DIAGRAM



FUNCTION TABLE ( X:H or L)

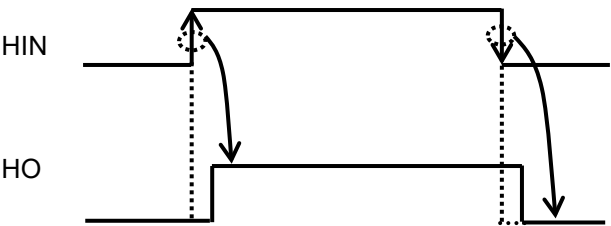
HIN	LIN	V <sub>BS</sub> UV	V <sub>CC</sub> UV	HO	LO	Behavioral state
H→L	L	H	H	L	L	HO = L, LO = L
H→L	H	H	H	L	H	LO = H
L→H	L	H	H	H	L	HO = H
L→H	H	H	H	L	L	HO = L, LO = L
X	L	L	H	L	L	LO=L,HO=L when V <sub>BS</sub> UV is detected
X	H	L	H	L	H	LO=H,HO=L when V <sub>BS</sub> UV is detected
H→L	X	H	L	L	L	LO=L,HO=L when V <sub>CC</sub> UV is detected
L→H	X	H	L	L	L	LO=L,HO=L when V <sub>CC</sub> UV is detected

Note1 : “L” state of V<sub>BS</sub> UV, V<sub>CC</sub> UV means that V<sub>CC</sub> (V<sub>BS</sub>) Supply become under UV trip voltage.

Note2 : In the case of both input signals (HIN and LIN) are “H”, output signals (HO and LO) become “L”.

Note3 : X(HIN):L→H or H→L    X(LIN):H or L

Note3 : Output Signal (HO) is triggered by the edge of input signal.

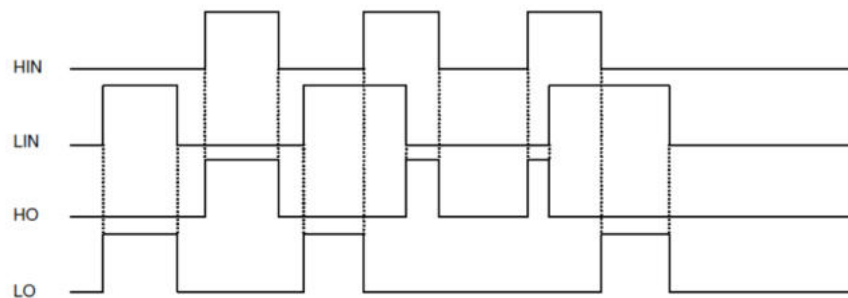


FUNCTION TIMING DIAGRAM

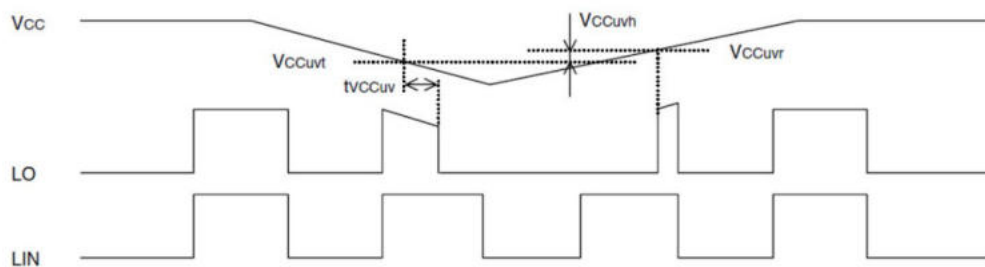
**1. Input/Output Timing Diagram**

High Active (When input signal (HIN or LIN) is "H", then output signal (HO or LO) is "H".)

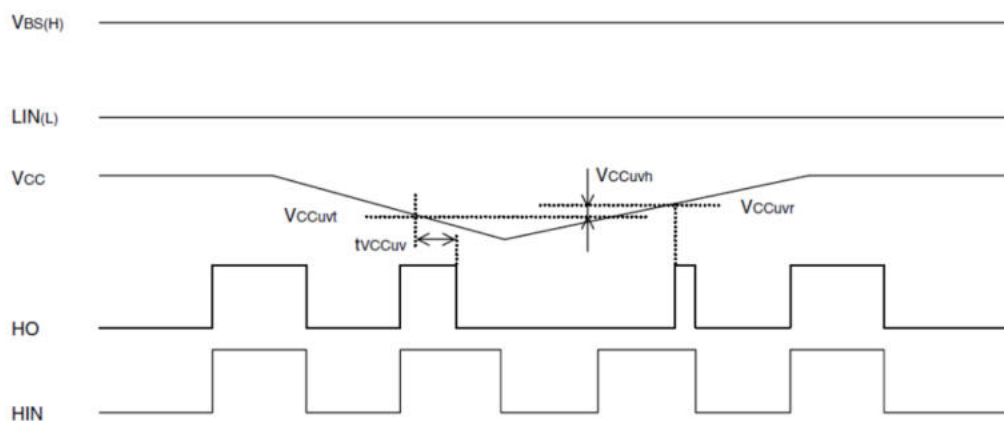
In the case of both input signal (HIN and LIN) are "H", output signals (HO and LO) become "L".

**2.  $V_{CC}$  ( $V_{BS}$ ) Supply Under Voltage (UV) Lockout Timing Diagram**

If  $V_{CC}$  supply voltage drops below UV trip voltage ( $V_{CCUVT}$ ) for  $V_{CC}$  supply UV filter time, LO output signal is shut down. And then, if  $V_{CC}$  supply voltage rises over UV reset voltage, LO will return to the usual operation mode.



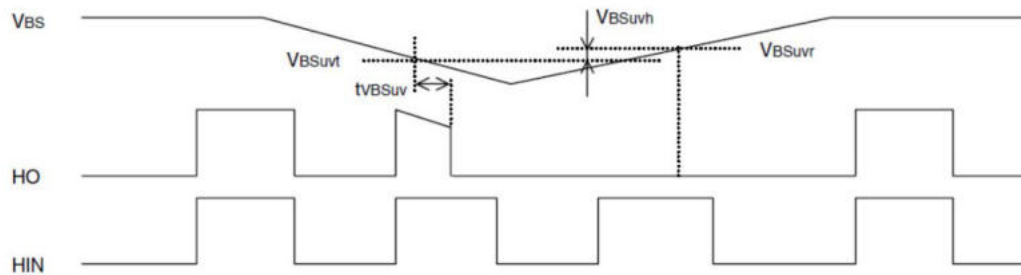
If  $V_{CC}$  supply voltage drops below UV trip voltage ( $V_{CCUVT}$ ) for  $V_{CC}$  supply UV filter time, HO output signal is shut down. And then, if  $V_{CC}$  supply voltage rises over UV reset voltage, HO will return to the usual operation mode.



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If  $V_{BS}$  supply voltage drops below UV trip voltage ( $V_{BSuvl}$ ) for  $V_{BS}$  supply UV filter time, HO output signal is shut down. And then, if  $V_{BS}$  supply voltage rises over UV reset voltage, HO will respond to the next active HIN signal(L→H).



**NOTES****1) Allowable supply voltage transient**

It is recommended to supply  $V_{CC}$  firstly and supply  $V_{BS}$  secondly. In the case of shutting off supply voltage, please shut off  $V_{BS}$  firstly and shut off  $V_{CC}$  secondly.

When applying  $V_{CC}$  and  $V_{BS}$ , power supply should be applied slowly.

If it rises rapidly, output signal (HO or LO) may be malfunction.

**2) Supply voltage start up or restart after shut down**

If  $V_{CC}$  supply is less than 10V(outside of RECOMMENDED OPERATING CONDITIONS), there is some possibility that output does not change in response to input.

Please evaluate carefully about supply start up or restart after shut down in your application systems.

**3)  $V_B$  supply voltage**

Please use  $V_B$  supply voltage within RECOMMENDED OPERATING CONDITIONS

( $V_S + 10V < V_B < V_S + 20V$  :  $V_S = 0V$  minimum)

If  $V_B$  supply voltage is used on the other conditions, output signal HO may be malfunction.

Please evaluate carefully about  $V_B$  supply voltage in your application systems.

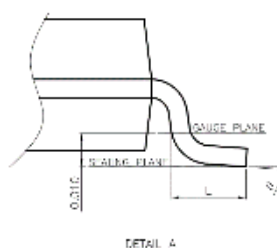
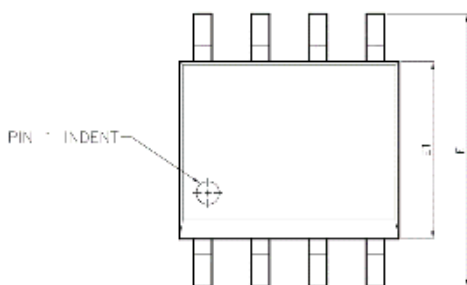
**4) Inter-terminal processing**

In this product, the terminal of the low voltage part and the high voltage part are adjacent (No.5: $V_{CC}$ , No.6: $V_S$ ). There may be cases where there is insufficient insulation clearance distance between the pins.

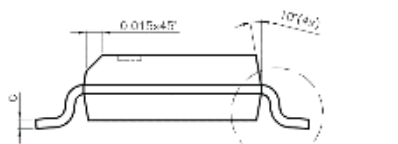
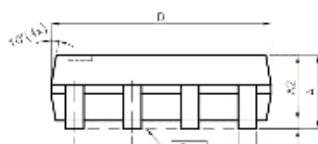
Please use such as coating between the terminals.

**ENVIRONMENTAL CONSCIOUSNESS**

M81776FP is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU+(EU)2015/863.

**PACKAGE OUTLINE**

SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
A	1.47	1.60	1.73
A1	0.10	—	0.25
A2	—	1.45	—
b	0.33	0.41	0.51
C	0.19	0.20	0.25
D	4.60	4.85	4.95
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	—	1.27	—
L	0.40	0.71	1.27
y	—	—	0.076
g	0	—	8



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
e1	—	5.23	—
l2	1.27	—	—
e	—	1.27	—
b2	—	0.76	—

The above is one example.

Please design the mount pad with your evaluation.

Recommended Mount Pad

M81776FP

### Main Revision for this Edition

Rev.	Date	Revision	
		Pages	Points
A	2 Apr. 2018	-	New
B	28 Apr. 2021	-	Delete "PRELIMINARY". Update format.



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